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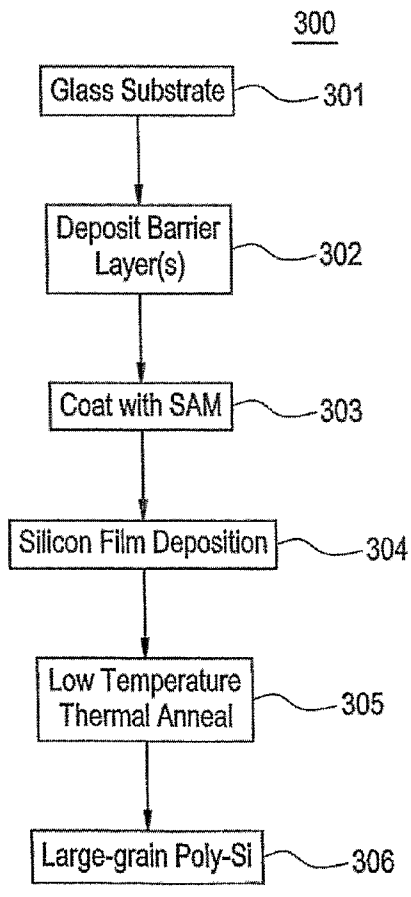
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(54) Title: SILICON CRYSTALLIZATION USING SELF-ASSEMBLED MONOLAYERS



(57) Abstract: A display device comprises a substrate having a layer of crystalline or polycrystalline semiconductor material disposed over the substrate, wherein the substrate has a strain point that is lower than a forming temperature of the layer. The crystalline or polycrystalline material is fabricated by a method that includes providing a self-assembled monolayer (SAM) over the substrate, depositing a layer of material over the SAM, and substantially crystallizing the layer.

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